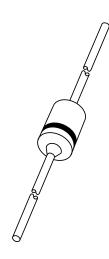
DISCRETE SEMICONDUCTORS

DATA SHEET



BYD63Ripple blocking diode

Product specification Supersedes data of November 1995 File under Discrete Semiconductors, SC01 1996 Jun 10





Ripple blocking diode

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FEATURES

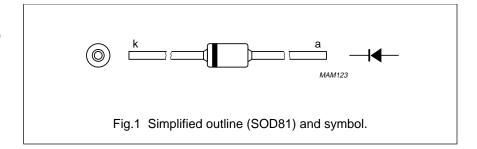
- Glass passivated
- High maximum operating temperature
- Low leakage current
- · Excellent stability
- Guaranteed minimum turn-on time for absorbing forward current transients and oscillations
- Specially designed as rectifier in the auxiliary power supply in e.g. switched mode power supplies
- Available in ammo-pack.

DESCRIPTION

Cavity free cylindrical glass package through Implotec $^{\text{TM}(1)}$ technology. This package is hermetically sealed

and fatigue free as coefficients of expansion of all used parts are matched.

(1) Implotec is a trademark of Philips.



LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V _{RRM}	repetitive peak reverse voltage		_	300	V
V_R	continuous reverse voltage		_	300	V
I _{F(AV)}	average forward current	averaged over any 20 ms period; $T_{tp} = 55$ °C; lead length = 10 mm; see Fig.2; see also Fig.4	_	0.85	A
		averaged over any 20 ms period; $T_{amb} = 65 ^{\circ}\text{C};$ PCB mounting (Fig.8); see Fig.3; see also Fig.4	_	0.45	A
I _{FRM}	repetitive peak forward current	T _{tp} = 55 °C	_	8.25	Α
		T _{amb} = 65 °C	_	4.45	Α
I _{FSM}	non-repetitive peak forward current	t = 10 ms half sine wave; $T_j = T_{j \text{ max}}$ prior to surge; $V_R = V_{RRMmax}$	_	5	A
T _{stg}	storage temperature		-65	+175	°C
Tj	junction temperature		-65	+175	°C

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ELECTRICAL CHARACTERISTICS

 $T_i = 25$ °C unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
V _F	forward voltage	$I_F = 1 \text{ A}$; $T_j = T_{j \text{ max}}$; see Fig.5	_	_	1.7	V
		I _F = 1 A; see Fig.5	_	_	2.3	V
I _R	reverse current	V _R = V _{RRMmax} ; see Fig.6	_	_	1	μΑ
		$V_R = V_{RRMmax}$; $T_j = 165 ^{\circ}\text{C}$; see Fig.6	_	_	100	μΑ
t _{fr}	forward recovery time	when switched to $I_F = 1 A$ in 50 ns; see Fig.9	_	_	350	ns
t _{on}	turn-on time	when switched from $V_F = 0 \text{ V}$ to $V_F = 3 \text{ V}$; measured between 10% and 90% of $I_{F \text{ max}}$; see Fig.11	500	-	_	ns
t _{rr}	reverse recovery time	when switched from $I_F = 0.5$ A to $I_R = 1$ A; measured at $I_R = 0.25$ A; see Fig.11	_	_	150	ns
C _d	diode capacitance	$f = 1 \text{ MHz}$; $V_R = 0 \text{ V}$; see Fig.7	_	17	_	pF

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
R _{th j-tp}	thermal resistance from junction to tie-point	lead length = 10 mm	60	K/W
R _{th j-a}	thermal resistance from junction to ambient	note 1	120	K/W

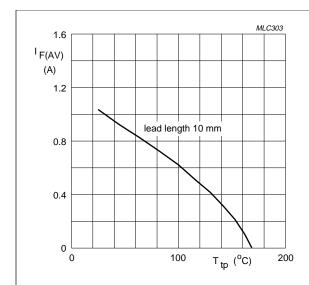
Note

1. Device mounted on an epoxy-glass printed-circuit board, 1.5 mm thick; thickness of Cu-layer ≥40 μm, see Fig.8. For more information please refer to the *'General Part of Handbook SC01.'*

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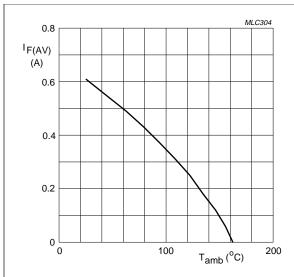
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GRAPHICAL DATA



 $a = 1.42; \ V_R = V_{RRMmax}; \ \delta = 0.5.$ Switched mode application.

Fig.2 Maximum permissible average forward current as a function of tie-point temperature (including losses due to reverse leakage).



 $\begin{aligned} &a=1.42;\ V_R=V_{RRMmax};\ \delta=0.5.\\ &\text{Device mounted as shown in Fig.8.}\\ &\text{Switched mode application.} \end{aligned}$

Fig.3 Maximum permissible average forward current as a function of ambient temperature (including losses due to reverse leakage).

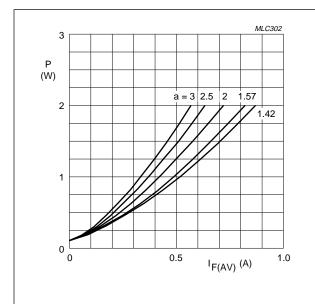
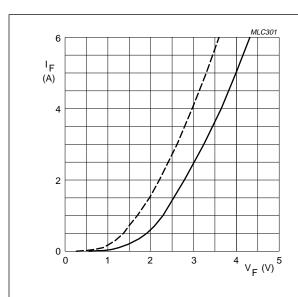


Fig.4 Maximum steady state power dissipation (forward plus leakage current losses, excluding switching losses) as a function of average forward current.



Dotted line: $T_j = 175 \,^{\circ}\text{C}$. Solid line: $T_j = 25 \,^{\circ}\text{C}$.

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Fig.5 Forward current as a function of forward voltage; maximum values.

 $a = I_{F(RMS)}/I_{F(AV)}$; $V_R = V_{RRMmax}$; $\delta = 0.5$.

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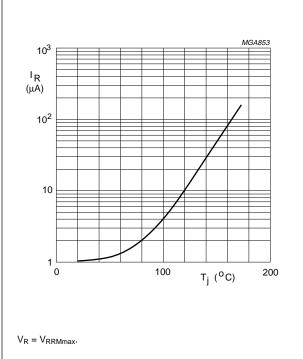


Fig.6 Reverse current as a function of junction temperature; maximum values.

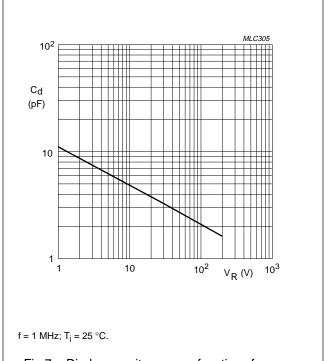
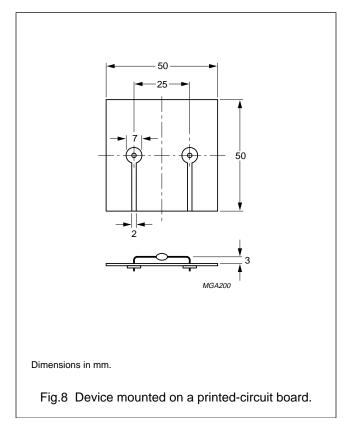
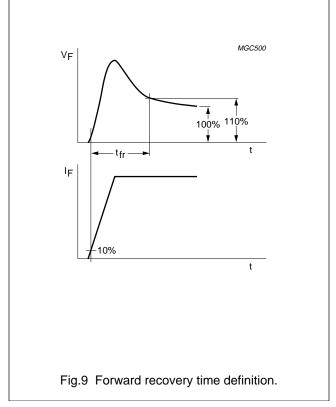


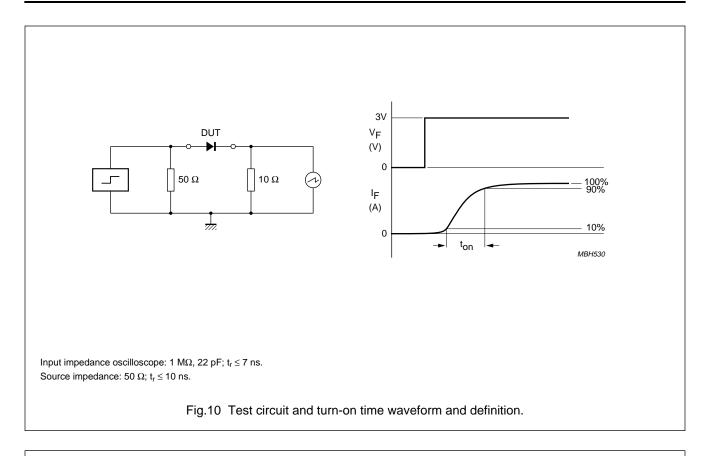
Fig.7 Diode capacitance as a function of reverse voltage; typical values.

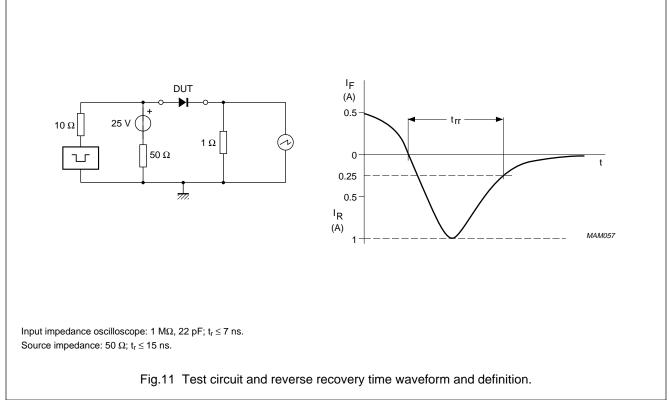




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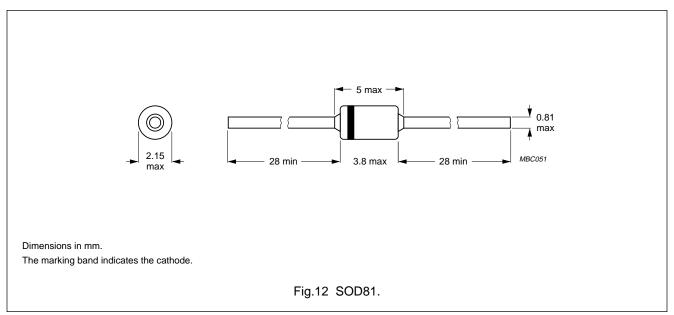




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PACKAGE OUTLINE



DEFINITIONS

Data Sheet Status	
Objective specification	This data sheet contains target or goal specifications for product development.
Preliminary specification	This data sheet contains preliminary data; supplementary data may be published later.
Product specification	This data sheet contains final product specifications.
Limiting values	

Limiting values

Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability.

Application information

Where application information is given, it is advisory and does not form part of the specification.

LIFE SUPPORT APPLICATIONS

These products are not designed for use in life support appliances, devices, or systems where malfunction of these products can reasonably be expected to result in personal injury. Philips customers using or selling these products for use in such applications do so at their own risk and agree to fully indemnify Philips for any damages resulting from such improper use or sale.